



### DMN3060LVT

# **Product Summary**

BV <sub>DSS</sub>	Rds(on)	I <sub>D</sub> T <sub>A</sub> = +25°C
30V	60mΩ @ V <sub>GS</sub> = 10V	3.6A
307	100mΩ @ V <sub>GS</sub> = 4.5V	2.7A

### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

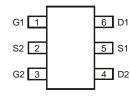
### **Mechanical Data**

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.013 grams (Approximate)

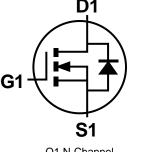


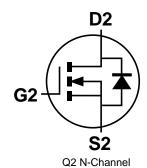
Top View

TSOT26



Top View





Q1 N-Channel

# Ordering Information (Note 4)

	Part Number	Case	Packaging				
	DMN3060LVT-7	TSOT26	3,000 / Tape & Reel				
	DMN3060LVT-13	TSOT26	10,000 / Tape & Reel				
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

				TSOT26	Ξ. M	Y Y	M = Date	uct Type M Code Marki x: G = 2019 (ex: 9 = Sep	ng ))	de		
Date Code Key												
Year	201	9	2020		2021	20	22	2023		2024	2	2025
Code	G		Н		I		J K L M					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) $V_{GS}$ = 4.5V	ID	3.6 2.8	A
Maximum Continuous Body Diode Forward Current (Note	Is	1.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	16	A

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.83	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R <sub>0JA</sub>	151	°C/W
Power Dissipation (Note 6)	PD	1.16	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R <sub>0JA</sub>	108	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

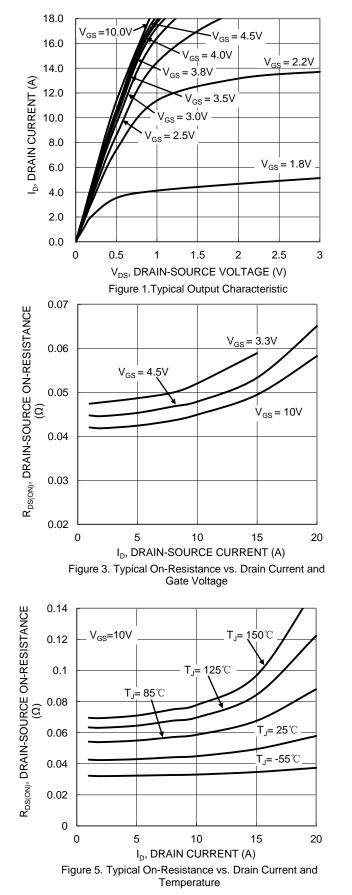
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
DFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$		
Gate-Source Leakage	IGSS		—	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.7	_	1.8	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$		
			42	60		$V_{GS} = 10V, I_D = 3.1A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	45	100	mΩ	$V_{GS} = 4.5V, I_D = 2A$		
			48	150		$V_{GS} = 3.3V, I_D = 1.5A$		
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.0	V	$V_{GS} = 0V, I_{S} = 1A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss		395	—				
Output Capacitance	C <sub>oss</sub>		39	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.2MHz		
Reverse Transfer Capacitance	Crss		26	-		1 = 1.200		
Gate Resistance	Rg	_	3.1	—	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qq		5.6	_		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.1A		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	11.3	—	nC			
Gate-Source Charge	Q <sub>qs</sub>		0.2	_	nc	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 3A		
Gate-Drain Charge	Q <sub>gd</sub>		1.8	_				
Turn-On Delay Time	t <sub>D(ON)</sub>		5.8	_				
Turn-On Rise Time	t <sub>R</sub>		30.8	—	20	$V_{GS} = 10V, V_{DS} = 15V,$		
Turn-Off Delay Time	t <sub>D(OFF)</sub>		18.3	—	ns	$R_G = 3\Omega, R_L = 4.7\Omega$		
Turn-Off Fall Time	t <sub>F</sub>		2.7	—				

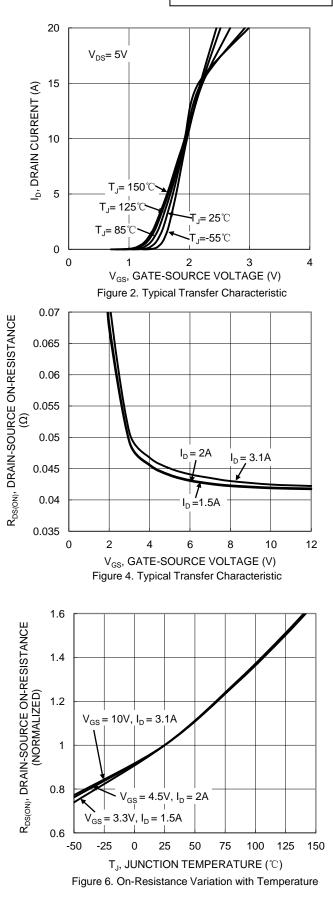
 Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect. Notes:

8. Guaranteed by design. Not subject to production testing.



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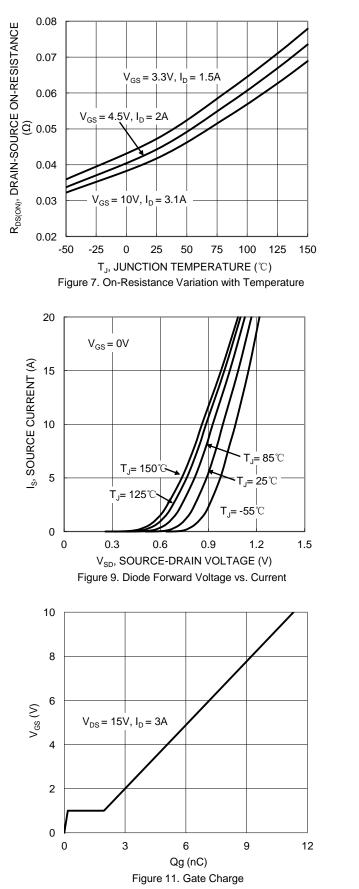


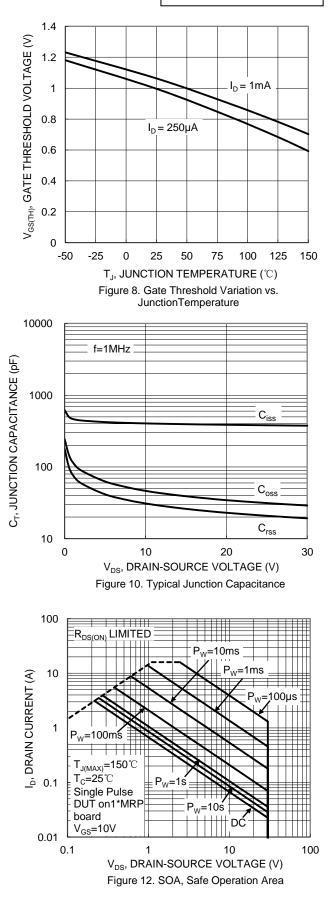


DMN3060LVT Document number: DS41714 Rev. 3 - 2

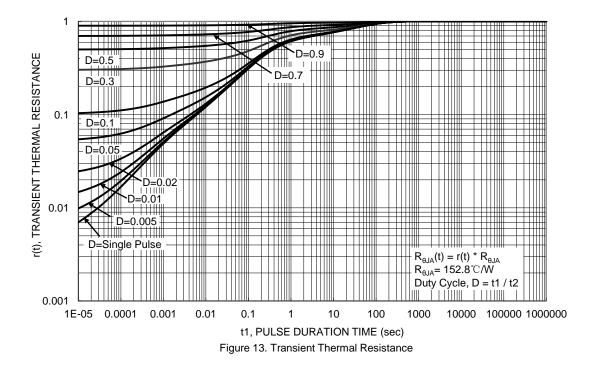


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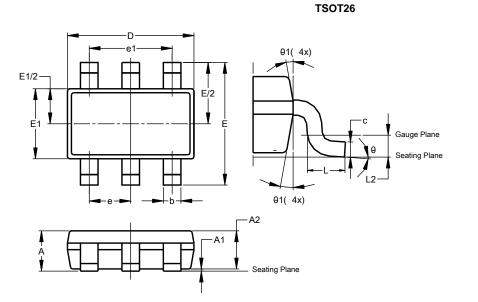






### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

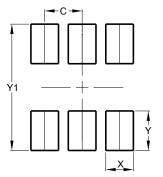


TSOT26								
Dim	Min	Max	Тур					
Α	-	1.00	-					
A1	0.010	0.100	-					
A2	0.840	0.900	-					
D	2.800	3.000	2.900					
Ш	2	2.800 BSC						
E1	1.500	0 1.700 1.						
q	0.300	0.450	-					
С	0.120	0.200	-					
e	0.950 BSC							
e1	1	.900 BS	С					
Г	0.30 0.50 -		-					
L2	0.250 BSC							
θ	0°	8°	4°					
θ1	4°	12°	-					
A	All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199

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